

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = +25°C (Note 5)	P _D	1	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

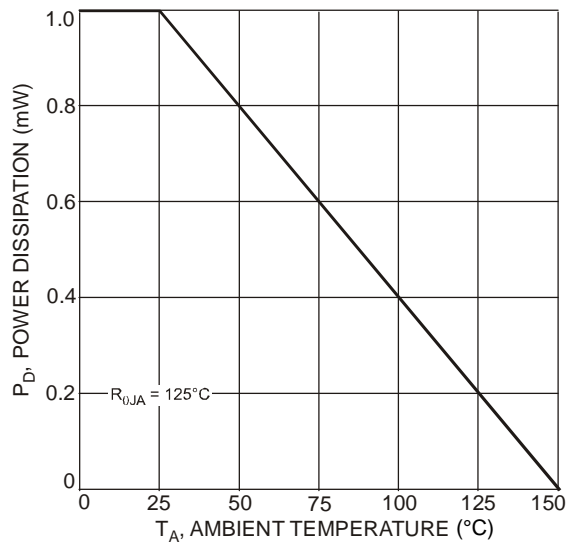


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-160	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-150	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	-50	nA	V _{CB} = -120V, I _E = 0
Emitter Cutoff Current	I _{EBO}	—	-50	nA	V _{CB} = -120V, I _E = 0, T _A = +100°C
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	50 60 50	— 240 —	—	V _{CE} = -5.0V, I _C = -1.0mA V _{CE} = -5.0V, I _C = -10mA V _{CE} = -5.0V, I _C = -50mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.2 -0.5	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-1.0	V	I _C = -10mA, I _B = -1.0mA I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	6.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{fe}	40	260	—	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = -10V, I _C = -10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V _{CE} = -5.0V, I _C = -200μA, R _S = 10Ω, f = 1.0kHz

Notes: 7. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

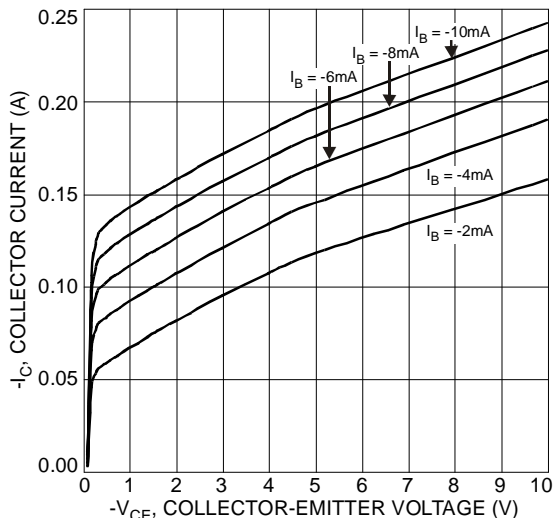


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

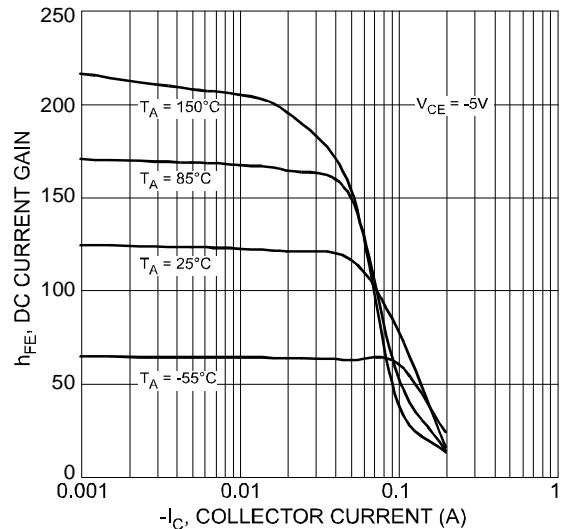


Fig. 3 Typical DC Current Gain vs. Collector Current

Typical Electrical Characteristics (Continued)

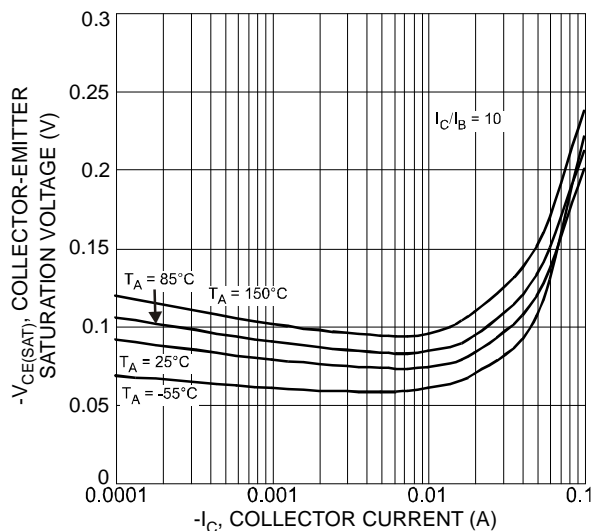


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

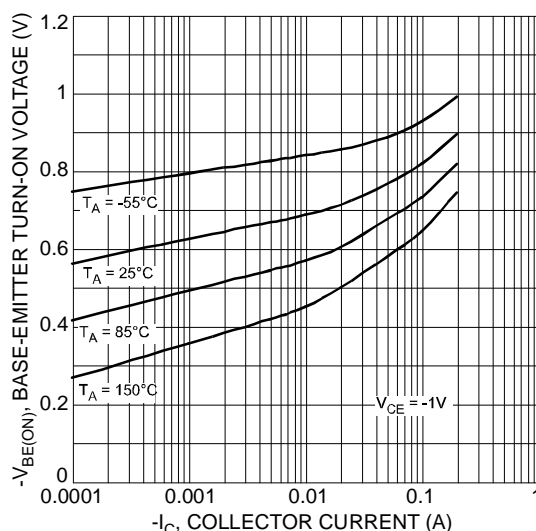


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

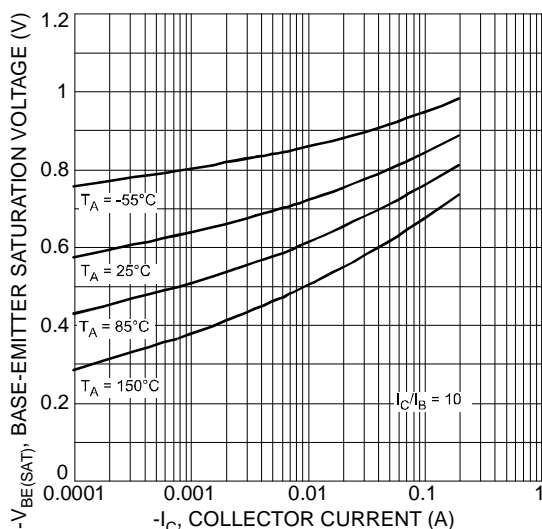


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

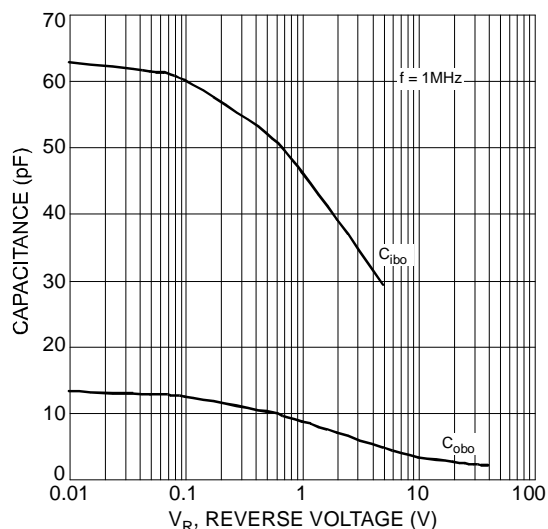


Fig. 7 Typical Capacitance Characteristics

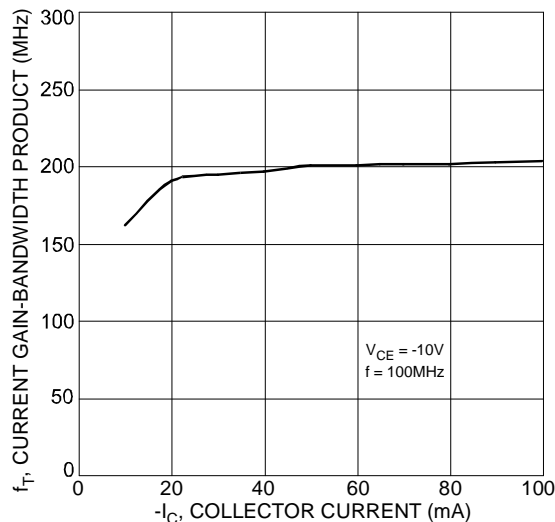
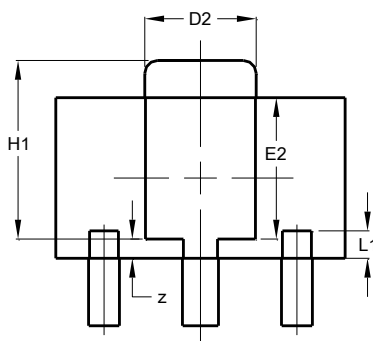
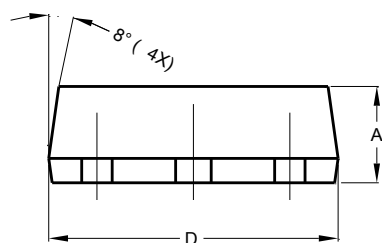
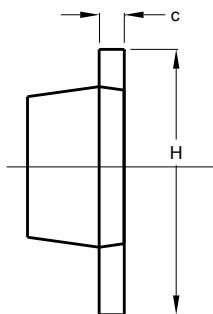
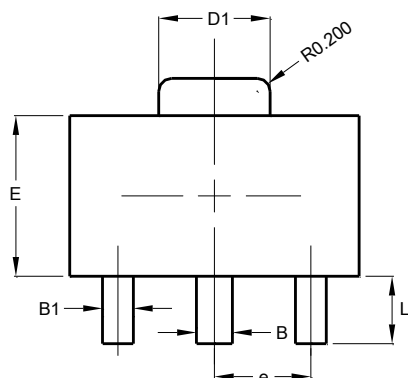


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89

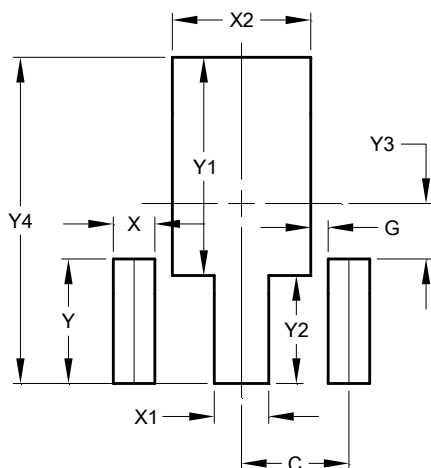


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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